

Amendments to the Claims

This listing of the claims will replace all prior versions, and listings, of claims in the application:

1. (amended) A [gaseous composition] process for forming an oxide composition comprising oxidizing a composition which is gaseous at a temperature below about 200° C. at atmospheric pressure, and which is adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass at a rate of deposition greater than about 350 Å/sec. wherein the composition comprises a precursor of tin oxide, a precursor of silicon oxide of formula  $R_m O_n Si_p$ , where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, an accelerant selected from the group consisting of organic phosphites, organic borates and water, and mixtures thereof, and a source of oxygen.
2. (amended) The [gaseous composition] process of claim 1, adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto transparent flat glass at a temperature of from 450° to about 650° C.
3. (amended) The [gaseous composition] process of claim 1, adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto transparent flat glass to produce a glass article having essentially no reflected color in daylight.
4. (amended) The [gaseous composition] process of claim 1 adapted to continuously deposit at least a first layer of tin oxide and silicon oxide onto a continuously moving transparent flat glass substrate.
5. (amended) The [composition] process of claim 1 where said composition is gaseous at a temperature below about 175° C.
6. (amended) The [composition] process of claim 1 wherein the organic phosphite and the

organic borate [accelerants] have the formula (R"O)<sub>3</sub> P and (R"O)<sub>3</sub> B where R" is independently chosen from straight, cyclic or branched-chain alkyl or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or R''' CH<sub>2</sub> CH<sub>2</sub> --, where R''' is MeO<sub>2</sub> C--, EtO<sub>2</sub> C--, CH<sub>3</sub> CO--, or HOOC--.

7. (amended) The [composition] process of claim 1 wherein the precursor of the tin oxide is R<sub>n</sub>SnX<sub>4-n</sub>, where R is a straight, cyclic, or branched-chain alkyl, or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or R'CH<sub>2</sub> CH<sub>2</sub> --, where R' is MeO<sub>2</sub> C--, EtO<sub>2</sub> C--, CH<sub>3</sub> CO--, or HO<sub>2</sub> C--; X is selected from the group consisting of halogen, acetate, perfluoroacetate, and their mixtures and where n is 0, 1, or 2.

8. (amended) The [composition] process of claim 1 wherein the precursor of the tin oxide is an alkyltin [chloride] halide.

9. (amended) The [composition] process of claim 1 wherein the precursor of the tin oxide is an alkyltin chloride.

10. (amended) The [composition] process of claim 1 wherein the precursor of the tin oxide is chosen from the group consisting of monobutyltin trichloride, dibutyltin dichloride, tributyltin chloride, and tin tetrachloride.

11. (amended) The [composition] process of claim 1 wherein the precursor of silicon oxide is selected from the group consisting of tetraethylorthosilicate, diacetoxymethyl-t-butoxysilane, ethyltriacetoxysilane, methyltriacetoxysilane, methyldiacetoxysilane, tetramethyldisiloxane, tetraramethylcyclotetrasiloxane, dipinacoloxysilane, 1,1-dimethylsila-2-oxacyclohexane, tetrakis (1-methoxy-2-propoxy) silane, and triethoxysilane.

12. (amended) The [composition] process of claim 1 wherein the precursor of silicon oxide is tetraethylorthosilicate.

13. (amended) The [composition] process of claim 1 wherein the accelerator comprises triethyl

phosphite.

14. (amended) The [composition] process of claim 1 wherein the accelerant comprises triethyl phosphite and triethyl borate.

15. (amended) The [gaseous composition] process of claim 1 adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass at a rate of deposition greater than about 400 Å/sec.

16. (amended) The [gaseous composition] process of claim 1 adapted to deposit at least a first amorphous layer of tin oxide and silicon oxide onto glass.

17. (amended) The [gaseous composition] process of claim 1 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass, the outermost layer of which is further adapted for deposit of at least a second layer.

18. (amended) The [composition] process of claim 17 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass, the outermost layer of which is further adapted for deposit of a layer comprising tin oxide.

19. (amended) The [composition] process of claim 17 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass the outermost layer of which is further adapted for deposit of a layer comprising tin oxide and fluorine.

20. (amended) The [composition] process of claim 17 wherein the second layer comprises a doped tin oxide.

21. (amended) The [composition] process of claim 17 wherein said plurality of layers are deposited from a precursor mixture comprising monobutyltin trichloride, tetrachethyl orthosilicate and triethyl phosphite.

22. (amended) The [composition] process of claim 1 adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto glass, said first layer having a refractive index which changes continuously between the glass substrate and the top of the layer.

23. (amended) A [gaseous composition] process fro forming an oxide composition comprising oxidizing a composition which is gaseous at a temperature below about 200° C. at atmospheric pressure, adapted to deposit at least a first amorphous layer comprising tin oxide and silicon oxide onto glass at a rate of deposition greater than about 400 Å/sec., the layer having a controlled index of refraction, wherein the composition comprises a tin oxide precursor, a silicon oxide precursor of formula  $R_mO_nSi_p$ , where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, and at least one accelerator chosen from the group consisting of boron and phosphorous esters and water.

24. (amended) The [gaseous composition] process of claim 23 adapted to continuously deposit at least a first layer comprising tin oxide and silicon oxide onto a continuously moving flat glass substrate at a temperature of from about 450° to about 650° C., and comprising monobutyltin trichloride, tetraethyl orthosilicate and an accelerator.

25. (amended) A [gaseous composition] process for forming an oxide composition comprising oxidizing a composition which is gaseous at a temperature below about 200° C. and at atmospheric pressure, and which is adapted to deposit at least a first layer comprising amorphous tin oxide and silicon oxide onto glass at a temperature of from about 450° to 650° C. at a rate of deposition greater than about 350 Å/sec., wherein the composition comprises:

a tin oxide precursor of formula  $R_nSnX_{4-n}$ , where R is a straight, cyclic, or branched-chain alkyl, or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or  $R'CH_2$   $CH_2^-$ , where R' is  $MeO_2C^-$ ,  $EtO_2C^-$ ,  $CH_3CO^-$ , or  $HO_2C^-$ ; X is selected from the group consisting of halogen, acetate, perfluoroacetate, and their mixtures; and where n is 0, 1, or 2;

a silicon oxide precursor of formula  $R_m O_n Si$ , where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl;

one or more accelerants selected from the group consisting of water and organic phosphites and organic borates of formula  $(R''O)_3 P$  and  $(R''O)_3 B$  where  $R''$  is independently chosen from straight, cyclic or branched-chain alkyl or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or  $R''' CH_2 CH_2 -$ , where  $R'''$  is  $MeO_2 C-$ ,  $EtO_2 C-$ ,  $CH_3 CO-$ , or  $HOOC-$ ; and

a source of oxygen.

26. (amended) A [composition] process according to claim 25 in which the precursor of the tin oxide is an alkyltin halide, the precursor of the silicon oxide is tetraethylorthosilicate, diacetoxidi-t-butoxysilane, ethyltriacetoxysilane, methyltriacetoxysilane, methyldiacetoxysilane, tetramethyldisiloxane, tetramethylcyclotetrasiloxane, dipinacoloxysilane, 1,1-dimethylsila-2-oxacyclohexane, tetrakis (1-methoxy-2-propoxy) silane, or triethoxysilane, and the accelerant comprises one or both of triethyl phosphite and triethyl borate.

27. (amended) A [composition] process according to claim 26 in which the tin oxide precursor comprises monobutyltin trichloride, the silicon oxide precursor comprises tetraethyl orthosilicate and the accelerant comprises triethyl phosphite.